

Ref #	Hits	Search Query	DBs	Default Operator	Plurals	Time Stamp
L1	122	((semiconductor adj3 memory) same (cell\$3 adj3 block\$2)) same (stor\$2 adj3 data)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/17 14:47
L2	10	((semiconductor adj3 memory) same (cell\$3 adj3 block\$2)) same (stor\$2 adj3 data) same redundancy	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/17 14:48
L3	45	(cell adj3 block) same (stor\$3 adj4 data) same redundancy	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/17 14:48
L4	9	((cell adj3 block) same (stor\$4 adj3 data) same redundancy) and ECC	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/17 14:48
L5	5	((semiconductor adj3 memory) same (cell\$4 adj3 block\$2)) and 365/200,201,225.7.ccls.) and redundancy and ECC	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/17 14:48
L6	101	((semiconductor adj4 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.) and repair) and redundanc\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/17 14:48
L7	100	((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.) and repair) and redundanc\$3) and ((semiconductor adj3 memory) same (cell\$2 adj4 block\$2))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/17 14:49
L8	3	((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.) and repair) and redundanc\$3) and ((semiconductor adj3 memory) same (cell\$4 adj3 block\$2)) same (stor\$2 adj3 data))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/17 14:49
L9	13	((cell adj3 block) same (stor\$3 adj3 data) same redundancy) and ((semiconductor adj3 memory) same (cell\$4 adj3 block\$2)) and 365/200,201,225.7.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/17 14:49

L10	9	((cell adj3 block) same (stor\$3 adj3 data) same redundancy) and ((semiconductor adj3 memory) same (cell\$2 adj3 block\$3)) and 365/200,201,225.7.ccls.) and (((((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.) and repair) and redundanc\$3) and "365"/\$7.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/17 14:49
S1	2172	(semiconductor adj3 memory) same (cell\$2 adj3 block\$2)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 03:01
S2	107	((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) same (stor\$2 adj3 data)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/17 14:47
S3	8	((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) same (stor\$2 adj3 data)) same redundancy	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/17 14:48
S4	38	(cell adj3 block) same (stor\$3 adj3 data) same redundancy	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/17 14:48
S5	6	((cell adj3 block) same (stor\$3 adj3 data) same redundancy) and ECC	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/17 14:48
S6	378	((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 03:01
S7	4	((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.) and redundancy and ECC	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/17 14:48
S8	14	choi-sung-h.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 03:02

S9	433	choi-sung-\$.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 03:02
S10	2	choi-sung.in.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 03:02
S11	0	(((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.) and ECC and repair	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 03:04
S12	118	(((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.) and repair	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 03:04
S13	94	(((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.) and repair) and redundanc\$3	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/17 14:48
S14	94	((((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.) and repair) and redundanc\$3) and "365"/\$7.ccls.	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2004/10/18 03:04
S15	94	((((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.) and repair) and redundanc\$3) and ((semiconductor adj3 memory) same (cell\$2 adj3 block\$2))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/17 14:49
S16	3	((((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.) and repair) and redundanc\$3) and (((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) same (stor\$2 adj3 data))	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/17 14:49
S17	12	((cell adj3 block) same (stor\$3 adj3 data) same redundancy) and (((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/17 14:49

S18	8	(((cell adj3 block) same (stor\$3 adj3 data) same redundancy) and (((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.)) and ((((((semiconductor adj3 memory) same (cell\$2 adj3 block\$2)) and 365/200,201,225.7.ccls.) and repair) and redundanc\$3) and "365"/\$7.ccls.)	US-PGPUB; USPAT; EPO; JPO; DERWENT; IBM_TDB	OR	ON	2005/04/17 14:49
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